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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
09/849,530	05/07/2001	Vincent J. McGahay	F19-98-172US2	1010		
32074	7590 12 04 2002					
INTERNAT	INTERNATIONAL BUSINESS MACHINES CORPORATION			EXAMINER		
DEPT. 18G BLDG. 300-4	182	MALDONADO, JULIO J				
2070 ROUTE 52 HOPEWELL JUNCTION, NY 12533		ART UNIT	PAPER NUMBER			
	,		2823			
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Please find below and/or attached an Office communication concerning this application or proceeding.



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		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
APPLICATION NO.	FILING DATE	Vincent J. McGahay	F19-98-172US2	1010	
09/849,530	05/07/2001		117-70-172002		
	90 02/14/2002		EXAMINER		
Connolly Bove	emick, Esquire Lodge & Hutz LLP		COLLINS, DEVEN M		
Suite 800 1990 M Street,	N.W.		ART UNIT	PAPER NUMBER	
Washington, D	C 20036-3425		2823		

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4		Application	No.	Applicant(s)	
		09/849,530		MCGAHAY ET AL.	5.1
	Office Action Summary	Examiner		Art Unit	
		Julio J. Maldo	nado	2823	·
Period fo	The MAILING DATE of this communication				ess
THE I - Exter after - If the - If NO - Failu - Any r	ORTENED STATUTORY PERIOD FOR REMAILING DATE OF THIS COMMUNICATION makings of time may be available under the provisions of 37 CF SIX (6) MONTHS from the mailing date of this communication period for reply specified above is less than thirty (30) days, a period for reply is specified above, the maximum statutory pere to reply within the set or extended period for reply will, by streply received by the Office later than three months after the modern patent term adjustment. See 37 CFR 1.704(b)	DN. R 1.136(a) In no event, I a reply within the statutory riod will apply and will ex- atute, cause the applicati	nowever, may a reply be tim minimum of thirty (30) day: bire SIX (6) MONTHS from on to become ABANDONE	rely filed s will be considered timely the mailing date of this comm D (35 U S C § 133)	unication
1)[∑]	Responsive to communication(s) filed on	18 April 2002			
2a)		This action is no	n-final.		
3)☐ Dispositi	Since this application is in condition for all closed in accordance with the practice uncon of Claims	owance except fo	r formal matters, pr		nerits is
4)⊳	Claim(s) 15-30 is/are pending in the applic	ation.			
	4a) Of the above claim(s) is/are with	drawn from consid	leration.		
	Claim(s) is/are allowed.				
6)[Claim(s) <u>15-17,20,21 and 26-30</u> is/are rejective.	cted.			
	Claim(s) <u>18,19 and 22-25</u> is/are objected to				
	Claim(s) are subject to restriction an		irement.		
	on Papers	·			
9) 🗌 -	The specification is objected to by the Exam	niner.			
10) 🔲 🛭	Fhe drawing(s) filed on is/are: a)☐ a	ccepted or b) obj	ected to by the Exar	niner.	
	Applicant may not request that any objection to	the drawing(s) be	held in abeyance. Se	e 37 CFR 1.85(a).	
11) 🔲 🏻	The proposed drawing correction filed on	is: a) 🔲 appro	oved b) disappro	ved by the Examiner.	
	If approved, corrected drawings are required in	reply to this Office	action.		
12) 🔲 T	The oath or declaration is objected to by the	Examiner.			
riority u	nder 35 U.S.C. §§ 119 and 120				
13)	Acknowledgment is made of a claim for fore	eign priority under	35 U.S.C. § 119(a)	-(d) or (f).	
a)[☐ All b)☐ Some * c)☐ None of:				
	1. Certified copies of the priority docume	ents have been re	ceived.		
	2. Certified copies of the priority docume	ents have been re	ceived in Application	n No	
	 Copies of the certified copies of the p application from the International ee the attached detailed Office action for a 	Bureau (PCT Rul	e 17.2(a)).		ge
14) 🗌 A	cknowledgment is made of a claim for dome	estic priority under	35 U.S.C. § 119(e) (to a provisional ap	plication)
	☐ The translation of the foreign language cknowledgment is made of a claim for dome				
ttachment		, , ,	33 - 40		
!) 🔲 Notice	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449) Paper No(s	4) [5) [6) [_	(PTO-413) Paper No(s) _atent Application (PTO-15	
Patent and Tra O-326 (Rev	idemark Office 04-01) Office	Action Summary		Part of Papi	er No. 10

Art Unit: 2823

DETAILED ACTION

1. The non-final rejection as set forth in paper No. 5 is withdrawn in response to applicants' request for reconsideration.

- 2. A new rejection is made as set forth in this Office Action.
- 3. Claims 15-30 are pending in the application.

Claim Rejections - 35 USC § 103

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 5. Claims 15-17, 20, 21 and 26-29 are rejected under 35 U.S.C. 103(a) as being unpatentable over Van Ngo et al. (U.S. 6,153,523) in view of Joshi et al. (U.S. 5,420,069).

In reference to claim 15-17, 26 and 29, Van Ngo et al. (Figs.1-4) in a related method to form a copper damascene structure, teach the steps of providing a germanium-containing layer (30) onto at least one surface of a copper member (13A); and providing a layer of silicon nitride (40) on the germanium-containing layer (30), wherein the copper member comprises copper or a copper alloy, wherein silicon nitride does not adhere well to the copper (column 3, line 38 – column 7, line 7).

Van Ngo et al. fail to teach forming that the layer of germanium-containing layer comprises copper germanide. However, Joshi et al. (Figs.2A-2B) in a related method to form a copper damascene structure teach providing a layer of copper germanide (100)

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over a layer of copper (80) by flowing germane over the structure at a temperature of 200 to 450°C (column 2, line 9 – column 3, line 3). Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention was made to form copper germanide as taught by Joshi et al. in the copper damascene structure of Van Ngo et al., since this would prevent corrosion of the copper surface (column 2, lines 45-53).

In reference to claims 20, 21, 27 and 28, Van Ngo et al. in combination with Joshi et al. substantially teach all aspects of the invention but fail to show forming the copper germanide layer to a thickness of about 100 to about 1,000Å; forming the copper member to a thickness of about 1,000 to about 20,000Å; and forming the layer of silicon nitride to a thickness of about 100 to about 20,000Å. However, the selection of the claimed range is obvious because it is a matter of determining optimum process condition by routine experimentation with a limited number of species. In re Jones, 162 USPQ 224 (CCPA 1955)(the selection of optimum ranges within prior art general conditions is obvious) and In re Boesch, 205 USPQ 215 (CCPA 1980)(discovery of optimum value of result effective variable in a known process is obvious).

6. Claim 30 is rejected under 35 U.S.C. 103(a) as being unpatentable over Van Ngo et al. ('523) in view of Joshi et al. ('069) as applied to claims 15-17, 20, 21 and 26-29 above, and further in view of Applicants' admitted prior art in the instant application.

Van Ngo et al. in combination with Joshi et al. substantially teach all aspects of the invention but fail to teach providing silicon oxide over the germanium containing layer, wherein silicon oxide does not adhere well to the copper surface. However, the

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prior art teach that silicon oxide does not adhere well to a copper surface (page 1, line 9 – page 2, line 28). Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention was made to provide silicon oxide as taught by the prior art in the copper damascene formation method of Van Ngo et al. and Joshi et al., since silicon oxide is a common material used in the formation of dielectric layers.

Allowable Subject Matter

- 7. Claims 18, 19, 22-25 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.
- 8. The following is a statement of reasons for the indication of allowable subject matter:

The prior art of record, Van Ngo et al. U.S. 6,153,523 teach a related method to form a copper damascene structure the steps of providing a germanium-containing layer (30) onto at least one surface of a copper member (13A); and providing a layer of silicon nitride (40) on the germanium-containing layer (30), wherein the copper member comprises copper or a copper alloy, wherein silicon nitride does not adhere well to the copper (column 3, line 38 – column 7, line 7). However, Van Ngo et al. neither teach nor suggest the a germanium-containing layer comprising copper germanide, copper oxide, copper nitride or combinations thereof over the copper member; and providing a gaseous composition comprising about 0.05 to about 5% of germane and a second gas selected from the group consisting of nitrogen, helium, argon, and mixtures thereof.

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Joshi et al. to 5,420,069 (Figs.2A-2B and column 2, line 9 – column 3, line 3) teach a method of forming a copper damascene including forming copper germanide layer (100) over a copper member (80) by flowing germane over the copper member (80). However, Joshi et al. neither teach nor suggest forming germanium nitride, germanium oxide or combinations thereof; and forming the germanium containing layer by providing a gaseous composition comprising about 0.05 to about 5% of germane and a second gas selected from the group consisting of nitrogen, helium, argon, and mixtures thereof.

Response to Arguments

9. Applicant's arguments with respect to claims 15-30 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

10. Papers related to this application may be submitted directly to Art Unit 2823 by facsimile transmission. Papers should be faxed to Art Unit 2823 via the Art Unit 2823 Fax Center located in Crystal Plaza 4, room 3C23. The faxing of such papers must conform to the notice published in the Official Gazette, 1096 OG 30 (15 November 1989). The Art Unit 2823 Fax Center number is (703) 305-3432. The Art Unit 2823 Fax Center is to be used only for papers related to Art Unit 2823 applications.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to **Julio J. Maldonado** at **(703) 306-0098** and between the hours of 8:00 AM to 4:00 PM (Eastern Standard Time) Monday through Friday or by e-mail via julio.maldonado@uspto.gov. If attempts to reach the examiner by telephone

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are unsuccessful, the examiner's supervisor, Olik Chaudhuri, can be reached on (703) 306-2794.

Any inquiry of a general nature or relating to the status of this application should be directed to the **Group 2800 Receptionist** at **(703) 308-0956**.

Julio J. Maldonado
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Hill Chandra

Supervisory Patent Examine: Technology Carte, 1900